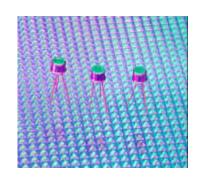
### TO-46, 2.5Gbps VCSEL

### **Product Description**

The TO-46, 2.5Gbps VCSEL is a high-performance, near-infrared, 850nm VCSEL (Vertical Cavity Surface-Emitting Laser) tailored to meet the needs of high-speed data communications and telecommunications applications. The product is designed for easy integration into a wide variety of Gigabit Ethernet, Fibre Channel, and ATM transceiver modules and systems.



### **Product Specifications**

### **Absolute Maximum Ratings**

Parameter	Rating	Important Notice		
Operating Case Temperature	0°C to 85°C	Stresses beyond those listed under "Absolute Maximun		
Storage Temperature	-40°C to 100°C	Ratings" may cause permanent damage to the device.  These are stress ratings only, and functional operation of		
Lead Solder Temperature	260°C for 10 seconds	the device at these or any other conditions beyond those		
Laser Reverse Voltage	5V	indicated for extended periods of time may effect device		
Laser Forward Current (continuous)	10mA	reliability.		
Laser Forward Current (instantaneous)	15mA			
Photodiode Forward Current	2mA			
Photodiode Reverse Voltage	10V			

## Electro-Optical Characteristics (T=25°C unless otherwise stated)

(. 25 5 4.1105 51.11.1105 51.11.54)							
Characteristic	Symbol	Min.	Тур.	Max.	Units		
Peak Emission Wavelength	$\lambda_{p}$	830	850	860	nm		
RMS Spectral Width	Δλ			0.85	nm		
λ Temp Coefficient	$\Delta \lambda_{ m p}$		0.06		nm/°C		
Optical Rise and Fall Time (20% - 80%)	$t_R$ , $t_F$		90	110	ps		
Threshold Current	I <sub>TH</sub>		1.5	2.5	mA		
Laser Forward Voltage (I <sub>Id</sub> =8mA)	$V_{F}$		1.8	2.2	V		
Relative Intensity Noise ( $I_{Id}$ =10mA, $f_0$ = 1GHz)	RIN		-128	-122	dB/Hz		
Differential Resistance (I <sub>Id</sub> =8mA)	δR		35	60	Ω		
Slope Efficiency (I <sub>th</sub> to 10mA)	η	.2	.3	.4	mW/mA		
Beam Divergence (Full width, 1/e <sup>2</sup> )	θ		27	32	deg		

# Photodiode Characteristics (T=25°C unless otherwise stated)

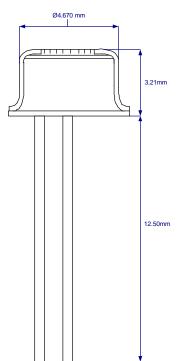
Characteristic	Symbol	Min.	Тур.	Max.	Units
Monitor Current (Id=8mA, Vrpd= -3V)	I <sub>PD</sub>	100	250	580	μΑ
Dark Current @ -3V bias	I <sub>D</sub>			20	nA
Capacitance @ 0V bias, 1 MHz	$C_{PD}$			100	pF

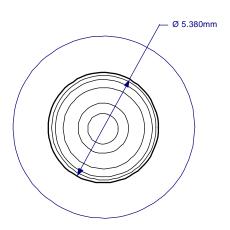


## TO-46, 2.5Gbps VCSEL

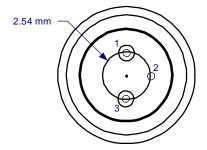
### Diagram

Dimensions are nominal



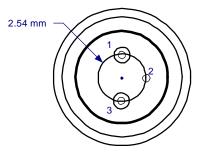


### 8585-8317: COMMON ANODE, ISOLATED



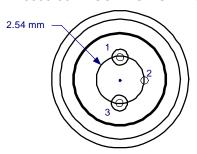
1-VCSEL CATHODE 2-PHOTODIODE ANODE 3-VCSEL ANODE/PHOTODIODE CATHODE

### 8585-8313: COMMON ANODE



1-VCSEL CATHODE 2-VCSEL ANODE/PHOTODIODE CATHODE 3-PHOTODIODE ANODE

### 8585-8312: COMMON CATHODE



1-VCSEL ANODE 2-VCSEL CATHODE/PHOTODIODE ANODE/CASE 3-PHOTODIODE CATHODE EMCORE Optical Devices 10420 Research Rd. SE Albuquerque, New Mexico 87123 USA Tel: (505)323-3400, Fax: (505)323-3402 E-mail: EODinfo@emcore.com

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